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A full-potential linear-muffin-tin-orbital study of water adsorption on and saturation in small Si clusters

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Abstract. The structure and geometrical parameters for water adsorption on a small-siliconcluster surface have been studied using the linear-muffin-tin-orbital method. We find that the most favoured adsorption site is the atop site of the capped atom for Si_5 , Si_6 , and Si_7 clusters. When H₂O adsorbs at such sites, the silicon clusters are elongated in the direction of the axis connecting one capped atom to another capped atom. Also, saturation studies have been performed. Each of these clusters can only adsorb two H₂O molecules at two atop sites of capped atoms. These clusters cannot adsorb any more H₂O molecules.

1. Introduction

The reactivity of silicon clusters containing from two to seventy atoms is very different from that of solid silicon [1]. Many experimental studies of the chemical reactions of silicon clusters with water have been performed. Using Fourier transform mass spectrometry (FTMS), Creasy *et al* [2] have carried out studies of the reactions of water with small-silicon-cluster cations (Si⁺₁₋₆). Their results show that reactions with H₂O are not observed for Si⁺₄₋₆, implying that the reactions proceed at rates which are less than 10^{-11} to 10^{-12} cm³ s⁻¹, i.e. it is difficult to get water to react with Si⁺₄₋₆ clusters. Ray and Jarrold [3] have studied the reaction between silicon-cluster cations (Si₁₀₋₆₅) and water using the injected-ion drift tube technique. Their results show that the only products observed for the reactions between the silicon-cluster cations and water were a series of Si_n(D₂O)⁺_m adducts. All of these experimental results corroborate the assertion that silicon clusters are relatively unreactive with water.

Very few theoretical studies have been performed on the reactivity of silicon clusters. Using the semiempirical molecular orbital (MO) method SINDO1 and the *ab initio* program Gaussian 90, Krack and Jug [4] have studied ammonia adsorption with neutral Si₅ and Si₁₀ clusters. We have studied the nature of NH₃-molecule adsorption and dissociation on neutral-Si-cluster surfaces by the DV- X_{α} method [5, 6] and the full-potential linear-muffin-tin-orbital (FP-LMTO) molecular dynamics method [7]. However, as far as we are aware, there have been no theoretical studies of water adsorption on silicon-cluster surfaces. There has been a gulf between experiment and theory. To achieve a deeper understanding of the properties of silicon clusters, such a theoretical study has some scientific importance.

In the present study, the most favoured adsorption site, the geometrical parameters, and the energy of adsorption of water on a neutral- Si_{5-7} -cluster surface are calculated by the FP-LMTO molecular dynamics method. Although many experimental results have been

obtained for water adsorbed by cation clusters, it is appropriate to discuss the results for neutral clusters; this is, in many cases, more scientifically interesting as regards different behaviours of clusters and extended surfaces. We also performed saturation studies. It is important to carry out such studies, because saturation studies can provide valuable information on the number and nature of the reactive sites, and the structure of the products [1].



Figure 1. The geometries of the lowest-energy structures of small silicon clusters. (*a*) Si₅. (*b*) Si₆. (*c*) Si₇. Side atoms: atoms 1–3 for Si₅; atoms 1–4 for Si₆; atoms 1–5 for Si₇. Capped atoms: atoms 4 and 5 for Si₅; atoms 5 and 6 for Si₆; atoms 6 and 7 for Si₇.

2. Models and the method

The most stable structures of Si_{5-7} clusters are the trigonal bipyramid (D_{3h}), the tetragonal bipyramid (D_{4h}), and the pentagonal bipyramid (D_{5h}), according to our accurate FP-LMTO molecular dynamics simulations (see figure 1). This is in good agreement with other theoretical results in [8–13]. According to the number of nearest-neighbour atoms, we can define two kinds of atom in Si_{5-7} (figure 1): capped atoms and side atoms [6]. On the basis of this definition, we try these possible adsorption sites: the atop site on the capped atom, the atop site on the side atom, the short-bridge site (between a capped atom and a side atom), the long-bridge site (between a side atom and a side atom). In our calculations, a water molecule will be placed at one such site, and then we start to calculate the adsorption energy and optimized structure by means of molecular dynamics simulations.

The calculated O–H bond length (0.98 Å) and H–O–H bond angle (103.5°) of free H_2O are adopted to compare with those of H_2O after adsorption (these data are in good



Figure 2. The adsorption and saturation sites for water on the Si_5 surface. (*a*) Adsorption at the atop site of capped atom 4. (*b*) Adsorption at the long-bridge site. (*c*) Saturation adsorption.

agreement with the experimental values: 0.96 Å and 104.5° [14]).

The FP-LMTO method [15–18] is a self-consistent implementation of the Kohn–Sham equations in the local-density approximation [19]. This method expands the electron wave functions in terms of muffin-tin orbitals [20]. Also this method uses a completely general form for the potential and density in which space is divided into non-overlapping muffin-tin spheres and the remaining interstitial region (in which the potential is expressed as a

linear combination of Hankel functions), instead of the atomic sphere approximation (ASA). The details of how the molecular dynamics simulation can be performed are described in references [17, 18].

3. Results and discussion

3.1. Adsorption

As a first step, we consider single-molecule adsorption. We will try all of the possible sites, and decide which is the most favoured adsorption site, and also calculate various parameters.

When a water molecule is adsorbed at the atop site of the capped atom of a Si₅ cluster (figure 2(*a*)), we find some changes in the structures of Si₅ and H₂O. All of these optimized adsorption geometries are shown in table 1. Because of the electron transfer from H₂O to Si₅, the H–O–H bond angle changes to 108.3° upon adsorption, which is 4.8° more than the value for the free H₂O molecule. The Si₅ cluster shows the same tendency as Si₅ + NH₃ [7], which is elongated in the direction of the axis connecting capped atoms 4 and 5. However, compared with Si₅ + NH₃, Si₅ encounters more difficulty in adsorbing H₂O. The adsorption energy is only 0.30 eV (0.86 eV for NH₃ adsorption). The structure of Si₅ also changes less than that of Si₅ + NH₃. The bond length between capped atom 4 and capped atom 5 (d_{4-5}) changes from 2.96 Å to 3.08 Å (3.14 Å for Si₅ + NH₃). The bond length between side atom 2 and side atom 3 (d_{2-3}) become shortened, from 3.04 Å to 2.94 Å (2.91 Å for Si₅ + NH₃). At the same time, the side atoms move toward the H₂O and away from the opposite capped atom (d_{1-4} changes from 2.29 Å to 2.28 Å, and d_{1-5} changes to 2.31 Å).

We now consider an H₂O molecule at the atop site of a side atom; there is no evidence that Si₅ can adsorb this molecule tightly (the adsorption energy is <0.05 eV). For the shortbridge site and the surface site, the findings are the same. However, Si₅ can adsorb an H₂O molecule on the long-bridge site with adsorption energy 0.20 eV (figure 2(*b*)).

We can conclude that the atop site of a capped atom is the most favourable for H_2O . According to our previous study [21], side atoms bind to each other via a many-centre bond, and this reduces their numbers of dangling bonds. At the same time, the capped atom binds to three side atoms, and has one dangling bond at its atop site. Thus the H_2O molecule is apt to adsorb at the atop site of the capped atom. On the other hand, a bond between a capped atom and a side atom is stronger than a bond between a side atom and a side atom (a many-centre bond), so H_2O can adsorb at a long-bridge site, but not at a short-bridge site.

(-,),										
	d_{1-2}	d_{1-5}	d_{1-6}	d_{5-6}	O–Si	O–H	$\theta_{\rm H-O-H}$	E_B (eV)		
Free Si ₆ and H ₂ O	2.72	2.35	2.35	2.69	_	0.98	103.5°	_		
$Si_6 + H_2O$ (capped)	2.70	2.33	2.37	2.74	2.33	0.98	107.4°	0.26		
$Si_6 + 2H_2O$	2.67	2.34	2.34	2.79	2.48	0.98	106.1°	0.35		

Table 1. Water adsorption and saturation geometrical parameters (Å), and adsorption energies (eV), for a Si₆-cluster surface.

Now we turn to water adsorption for a Si_6 cluster (figure 3 and table 1). Our findings are almost the same for $Si_6 + H_2O$ as for $Si_5 + H_2O$:

(1) the most favoured adsorption site for H₂O is the atop site of the capped atom



Figure 3. The adsorption and saturation sites for water on the Si₆ surface. (*a*) Adsorption at the atop site of capped atom 5. (*b*) Adsorption at the long-bridge site. (*c*) Saturation adsorption.

(adsorption energy: 0.26 eV; see figure 3(a));

(2) the H–O–H bond angle is bigger than the bond angle of free H_2O because of the electron transmission;

(3) the Si₆ cluster is elongated (all of the changes are the same as those for $Si_6 + H_2O$, although the changes are smaller);

(4) the long-bridge site can adsorb an H_2O molecule (adsorption energy: 0.19 eV; see figure 3(b));

(5) the short-bridge site, surface site, and atop site of a side atom cannot adsorb H_2O .

These results are easy to understand, because Si_6 , just like Si_5 , has many-centre bonds: four side atoms share a four-centre bond [7].

For Si₇ (figure 4 and table 2), we find that the most favoured site is the atop site of the capped atom (adsorption energy: 0.18 eV; see figure 4(*a*)). For such a site, the changes of structure for H₂O and Si₇ are same as those for Si₅ + H₂O and Si₆ + H₂O. However, H₂O cannot adsorb on the top of the side atom or at any other sites, even long-bridge sites. Because Si₇ is considered as five tetrahedra sharing a common edge formed by the two capped atoms [8], a side atom binds with all of its neighbouring atoms tightly [7]. This is the main reason that H₂O cannot adsorb at a long-bridge site.



Figure 4. The adsorption and saturation site for water on the Si_7 surface. (*a*) Adsorption at the atop site of capped atom 6. (*b*) Saturation adsorption.

Table 2. Water adsorption and saturation geometrical parameters (Å), and adsorption energies (eV), for a Si₇-cluster surface.

	d_{1-2}	d_{1-6}	d_{1-7}	d_{6-7}	O–Si	O–H	$\theta_{\rm H-O-H}$	E_B (eV)
Free Si ₇ and H ₂ O	2.47	2.45	2.45	2.49		0.98	103.5°	_
$Si_7 + H_2O$ (capped)	2.46	2.41	2.48	2.54	2.40	0.98	106.8°	0.19
$Si_7 + 2H_2O$	2.45	2.44	2.44	2.56	2.55	0.98	105.5°	0.23

As mentioned above, all Si_{5-7} clusters can adsorb H_2O molecules with very low adsorption energy ($\leq 0.30 \text{ eV}$). We think that Si_{5-7} -cation clusters encounter more difficulty in getting electrons from H_2O molecules; hence the adsorption energy will be smaller than that of neutral clusters, i.e. cation clusters will find it more difficult to adsorb H_2O . From

experimental results [2], we know that reactions with H_2O are not observed for Si_{5-7} -cation clusters, implying that they react with rates which are less than 10^{-10} to 10^{-11} cm³ s⁻¹. This supports our view that Si_{5-7} -cation clusters find it difficult to adsorb H_2O .

3.2. Saturation

In the preceding section, we investigated the single-molecule adsorption of H_2O . Now we turn to the saturation study, i.e. to deciding on the maximum number of H_2O molecules which Si_{5-7} clusters can adsorb.

Table 3. Water adsorption and saturation geometrical parameters (Å), and adsorption energies (eV), for a Si₅-cluster surface.

	d_{1-2}	d_{1-4}	d_{1-5}	d_{4-5}	O–Si	O–H	$\theta_{\rm H-O-H}$	E_B (eV)
Free Si ₅ and H ₂ O	3.04	2.29	2.29	2.96	_	0.98	103.5°	_
$Si_5 + H_2O$ (capped)	2.94	2.28	2.31	3.08	2.26	0.98	108.3°	0.30
$Si_5 + 2H_2O$	2.91	2.28	2.28	3.10	2.41	0.98	106.6°	0.45

After Si₅ has adsorbed an H₂O molecule at the atop site of the capped atom (atom 4), we put another H₂O molecule at the opposite site: the atop site on the capped atom 5 (figure 2(*c*)). The total adsorption energy is 0.45 eV—an increase of 0.15 eV on the single-H₂O-molecule adsorption energy (table 3). The strength of the bond between Si and O decreases. So the H–O–H bond angle (106.6°) becomes smaller than the single-moleculeadsorption bond angle (108.3°), and the length of the bond between Si and O is 2.41 Å, which is greater than the value of 2.26 Å for Si₅ + H₂O. The Si₅ cluster is more elongated: d_{4-5} is now 3.10 Å. The length of the bond between side atom 1 and side atom 2 (d_{1-2}) becomes shorter, decreasing from 2.94 Å to 2.91 Å.

However, from our further investigation, we found that we cannot put any more H_2O molecules at any possible adsorption sites of Si₅. So the maximum number of adsorbed H_2O molecules for a Si₅ cluster is two.

For Si₆ + 2H₂O, similar results have been obtained (figure 3(c)). We do not repeat them here. However, the increase of the adsorption energy is small: 0.09 eV (table 1). Si₆ cannot adsorb any more NH₃ molecules. It is difficult to say whether Si₇ can adsorb a second H₂O molecule (figure 4(b)), because the increase of the adsorption energy is only 0.04 eV. However, we provide all of the parameters in table 2.

4. Summary

We have studied H_2O adsorption and saturation for Si_{5-7} clusters. Our calculations show that the atop site of the capped atom is the most favoured site for Si_5 , Si_6 , and Si_7 clusters. When H_2O is adsorbed at such a site, the silicon clusters are elongated in the direction of the axis connecting a capped atom to a capped atom. Si_5 and Si_6 clusters can adsorb H_2O at long-bridge sites, although the adsorption energies are smaller. They cannot adsorb H_2O at other sites. But the Si_7 cluster cannot even adsorb H_2O at a long-bridge site. These results can be understood on the basis of the facts that Si_5 and Si_6 clusters form many-centre bonds, while Si_7 has a different bonding character.

For saturation adsorption, all of these clusters can only adsorb two H_2O molecules at two atop sites of capped atoms (for Si₇, it is difficult to say whether it can adsorb the second

 H_2O molecule, because the adsorption energy increase is only 0.04 eV). None of them can adsorb any more H_2O molecules.

Acknowledgments

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References

- [1] Jarrold M F 1991 Science 252 1085
- [2] Creasy W R, O'Keefe A and McDonald J R 1987 J. Phys. Chem. 91 2848
- [3] Ray U and Jarrold M F 1990 J. Chem. Phys. 94 2631
- [4] Krack M and Jug K 1995 Chem. Phys. 192 127
- [5] Qiu M, Lee L Q, Cao P L and Que D L 1997 J. Phys.: Condens. Matter 9 6543
- [6] Qiu M, Cao P L and Que D L 1998 Surf. Sci. 395 260
- [7] Qiu M, Zhou Xu-Yan, Jiang M, Cao P L and Zeng Z 1998 Phys. Lett. A at press
- [8] Raghavachari K 1990 Phase Transitions 24-26 61
- [9] Raghavachari K and Logovinsky V 1985 Phys. Rev. Lett. 55 2853.
- [10] Jing X, Troullier N, Cean D, Binggeli N, Chelikowsky J R, Wu K and Saad Y 1994 Phys. Rev. B 50 12 234
- [11] Binggeli N and Chelikowsky J R 1994 Phys. Rev. B 50 11764
- [12] Menon M and Subbaswamy K R 1993 Phys. Rev. B 47 12754
- [13] Ordejon P, Lebedenko D and Menon M 1994 Phys. Rev. B 50 5645
- [14] CRC Handbook of Chemistry and Physics 1993–1994 74th edn, ed D R Lide (Boca Raton, FL: Chemical Rubber Company Press)
- [15] Methfessel M 1988 Phys. Rev. B 38 1537
- [16] Methfessel M, Rodriguez C O and Andersen O K 1989 Phys. Rev. B 40 2009
- [17] Methfessel M and Schilfgaarde M V 1993 Int. J. Mod. Phys. B 7 262
- [18] Methfessel M and Schilfgaarde M V 1993 Phys. Rev. B 48 4937
- [19] Kohn W and Sham L J 1965 Phys. Rev. 140 A1133
- [20] Andersen O K 1975 Phys. Rev. B 12 3060
- [21] Qiu M, Zhou X Y, Jiang M, Cao P L and Que D L 1998 Chinese Phys. Lett. submitted